

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013 PHONE: (215) 631-9840 FAX: (215) 631-9855

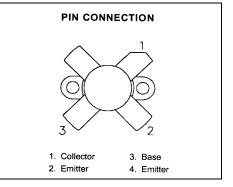
#### RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

## Features

- 30 MHz
- 28 VOLTS
- GOLD METALLIZATION
- **P**<sub>OUT</sub> = 220 W PEP
- $G_P = 12 \text{ dB GAIN MINIMUM}$
- COMMON EMITTER CONFIGURATION

## **DESCRIPTION:**

The MS1076 is a 28 volt epitaxial NPN silicon planar transistor designed primarily for SSB and VHF communications. This device utilizes an emitter ballasted die geometry for maximum ruggedness and reliability.



## ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit	
V <sub>сво</sub>	Collector - Base Voltage	70	V	
V <sub>CEO</sub>	Collector - Emitter Voltage	35	V	
<b>V</b> <sub>EBO</sub>	Emitter - Base Voltage	4.0	V	
c	Device Current	16	Α	
P <sub>DISS</sub>	Power Dissipation	320	W	
TJ	Junction Temperature	+200	°C	
Т <sub>stg</sub>	Storage Temperature	- 65 to +150	°C	

## **Thermal Data**

R <sub>TH(J-C)</sub>	Junction - Case Thermal Resistance	0.7	°C/W
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## MS1076

.500 4LFL (M174)

epoxy sealed



## MS1076

# ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Test Conditions			Value		
Symbol			Min.	Typ.	Max.	Unit
BV <sub>CES</sub>	I <sub>c</sub> = 100 mA	$V_{BE} = 0 V$	70			V
BV <sub>CEO</sub>	I <sub>c</sub> = 200 mA	I <sub>B</sub> = 0 mA	35			V
BV <sub>EBO</sub>	I <sub>E</sub> = 20 mA	I <sub>c</sub> = 0 mA	4.0			V
I <sub>CEO</sub>	$V_{CE} = 30 V$	I <sub>E</sub> = 0 mA			5	mA
I <sub>CES</sub>	V <sub>CE</sub> = 35 V	I <sub>E</sub> = 0 mA			5	mA
H <sub>FE</sub>	$V_{CE} = 5 V$	$I_{C} = 7 A$	15		50	

## DYNAMIC

Symbol	Test Conditions			Value			Unit
Symbol				Min. Typ. Max.			
Pout	f = 30 MHz	$V_{CE} = 28 V$	I <sub>CQ</sub> = 750 mA	220			WPEP
G <sub>P</sub>	f = 30 MHz	V <sub>CE</sub> = 28 V	I <sub>CQ</sub> = 750 mA	12			dB
ης	f = 30 MHz	V <sub>CE</sub> = 28 V	I <sub>CQ</sub> = 750 mA	40			%
IMD	f = 30 MHz	V <sub>CE</sub> = 28 V	I <sub>CQ</sub> = 750 mA			-30	dBc
Сов	f = 1 MHz	V <sub>CB</sub> = 28 V			450		pf
Conditioner	f1 _ 20 000	MH- +2 - 20.00					

Conditions: f1 = 30.000 MHz f2 = 30.001 MHz

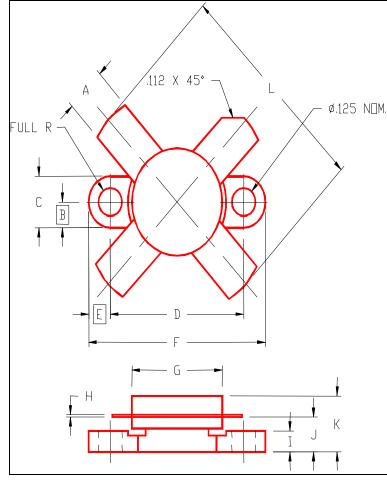
## **IMPEDANCE DATA**

FREQ	Z <sub>IN</sub>	Z <sub>CL</sub>
30 MHz	1.2 + j0.41	1.25 + j1.92



**MS1076** 

## PACKAGE MECHANICAL DATA



#### PACKAGE STYLE M174

	MINIMUM	MAXIMUM		MINIMUM	MAXIMUM
	INCHES/MM	INCHES/MM		INCHES/MM	INCHES/MM
Α	,220/5,59	,230/5,84	Ι	.090/2,29	.110/2,79
В	.125/	′3,18	J	,160/4,06	.175/4,45
С	.245/6,22	,255/6,48	К		.280/7,11
D	.720/18,28	.730/18,54	L		1.050/26,67
E	.125/3,18				
F	.970/24,64	.980/24,89			
G	,495/12,57	.505/12,83			
Н	.003/0,08	.007/0,18			